



# Product data sheet

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# BC856/57/58ABC HF (

Semiconductor Compiance





1. BASE 2. EMITTER

3. COLLECTOR

SOT - 23 DEVICE MARKING

P/N	MARK	P/N	MARK	P/N	MARK
BC856A	ЗA	BC856B	3B		
BC857A	3E	BC857B	3F	BC857C	3G
BC858A	3J	BC858B	3К	BC858C	3L

#### MAXIMUM RATINGS (T₂=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit	
V <sub>сво</sub>	BC856	-80	V	
	BC857	-50		
	BC858	-30		
	Collector-Emitter Voltage			
V <sub>CEO</sub>	BC856	-65	V	
	BC857	-45		
	BC858	-30		
V <sub>EBO</sub>	Emitter-Base Voltage		V	
lc	Collector Current –Continuous		А	
Pc	Collector Power Dissipation		mW	
R <sub>OJA</sub>	Thermal Resistance From Junction To Ambient		°C/W	
T <sub>J</sub> ,T <sub>stg</sub>	Operation Junction and Storage Temperature Range		°C	

#### ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter		Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage B	BC856			-80		
В	C857	V <sub>CBO</sub>	I <sub>C</sub> = -10μΑ, I <sub>E</sub> =0	-50		V
В	C858			-30		
Collector-emitter breakdown voltage B	BC856			-65		
В	C857	$V_{CEO}$	I <sub>C</sub> = -10mA, I <sub>B</sub> =0	-45		V
В	C858			-30		
Emitter-base breakdown voltage		$V_{\text{EBO}}$	Ι <sub>Ε</sub> = -1μΑ, Ι <sub>C</sub> =0	-5		V
Collector cut-off current B	C856		V <sub>CB</sub> = -70 V , I <sub>E</sub> =0			
В	SC857	I <sub>CBO</sub>	$V_{CB}$ = -45 V , I <sub>E</sub> =0		-0.1	μA
В	C858		$V_{\text{CB}}\text{=}$ -25 V , $I_{\text{E}}\text{=}0$			
Emitter cut-off current		I <sub>EBO</sub>	$V_{EB}\text{=-5 V}, \ I_{C}\text{=}0$		-0.1	μA
DC current gain BC856A, 857A	,858A			125	250	
BC856B, 857B	8,858B	h <sub>FE</sub>	$V_{CE}$ = -5V,I <sub>C</sub> = -2mA	220	475	
BC857C,BC	C858C			420	800	
Collector-emitter saturation voltage		V <sub>CE</sub> (sat)	I <sub>C</sub> =-100mA,I <sub>B</sub> = -5 mA		-0.5	V
Base-emitter saturation voltage		V <sub>BE</sub> (sat)	I <sub>C</sub> = -100mA, I <sub>B</sub> = -5mA		-1.1	V
Transition frequency		f⊤	V <sub>CE</sub> = -5 V, I <sub>C</sub> = -10mA f=100MHz	100		MHz
Collector capacitance		C <sub>ob</sub>	V <sub>CB</sub> =-10V, f=1MHz		4.5	pF

TRANSISTOR (PNP)

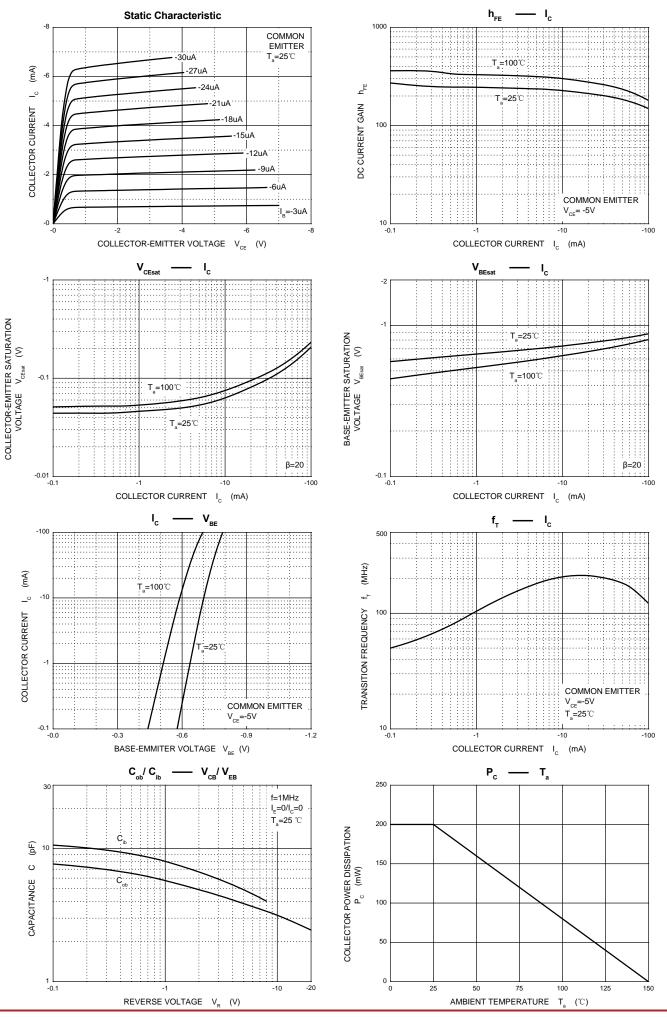
#### FEATURES

- Ideally suited for automatic insertion
- For Switching and AF Amplifier Applications



BC856/57/58ABC HF 🔬

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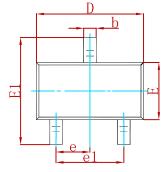
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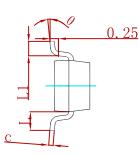


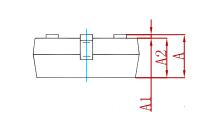


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#### PACKAGE MECHANICAL DATA

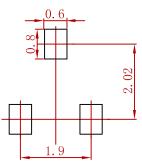






Symbol	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min	Max	Min	Max	
A	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

#### Suggested Pad Layout



Note:

Controlling dimension:in millimeters.
General tolerance:± 0.05mm.
The pad layout is for reference purposes only.

#### **REEL SPECIFICATION**

P/N	PKG	QTY
BC856/57/58ABC	SOT-23	3000



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